A 1.0 Watt GaAs MESFET Oscillator at X-Band

R.M. Rector and G.D. Vendelin. "A 1.0 Watt GaAs MESFET Oscillator at X-Band." 1978 MTT-S International Microwave Symposium Digest 78.1 (1978 [MWSYM]): 145-146.

The design and performance of high power GaAs MESFET oscillators are described for two commercially available MESFET transistors. The oscillators were fabricated with packaged common-gate transistors on microstrip circuits. Power levels, and efficiencies are comparable to amplifier performance at the same frequency.

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